

FIG. 1A

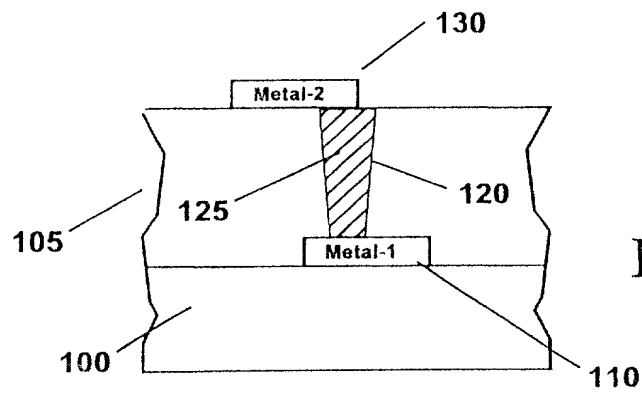


FIG. 1B

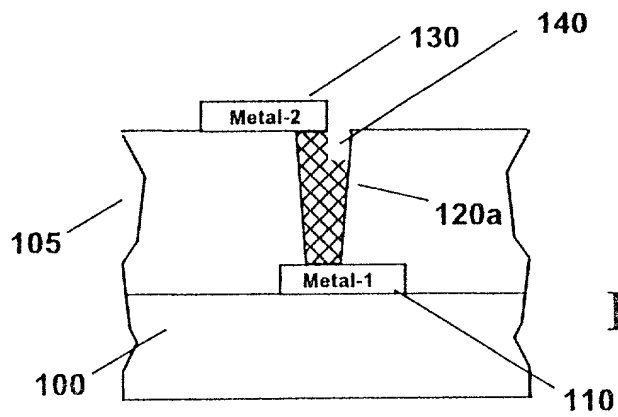
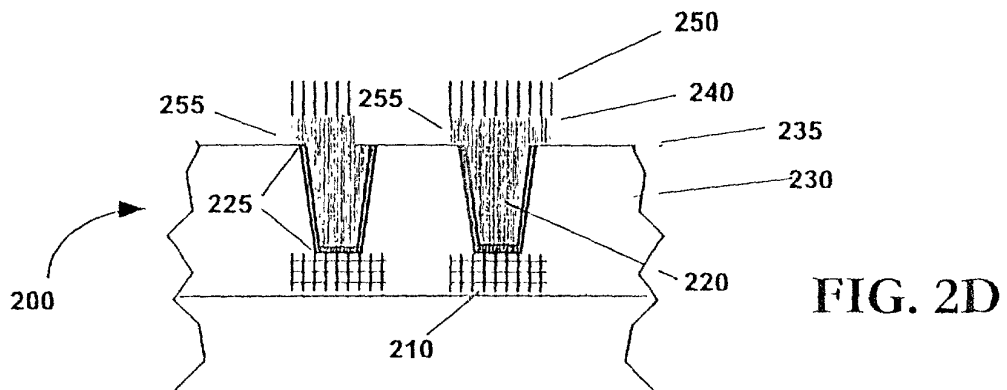
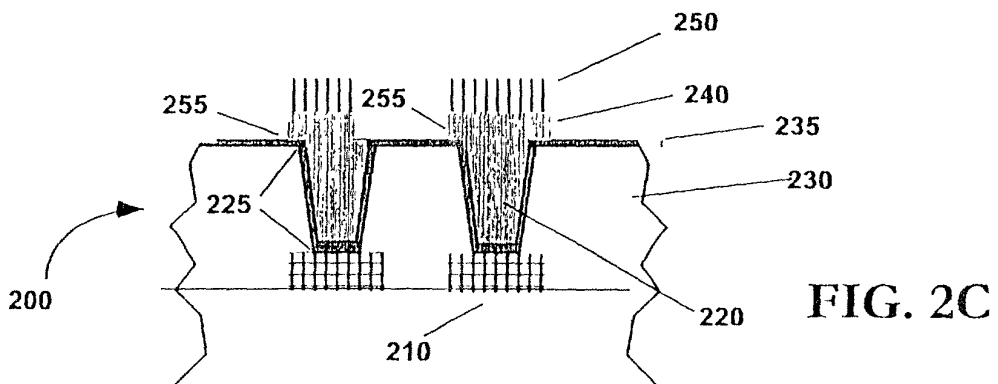
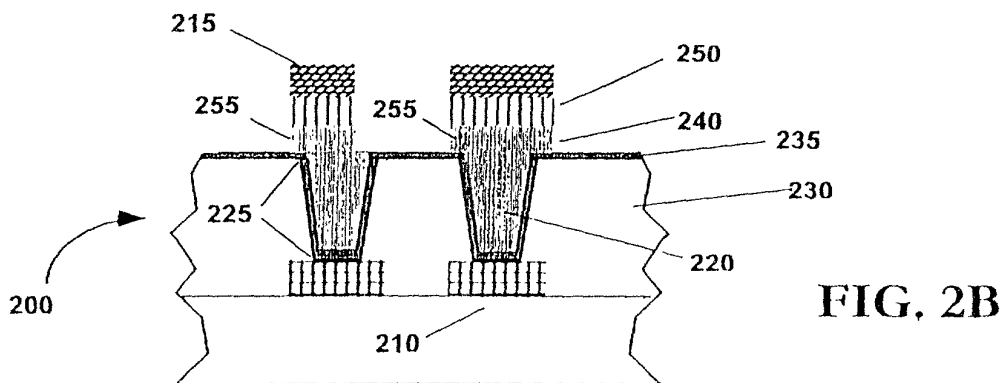
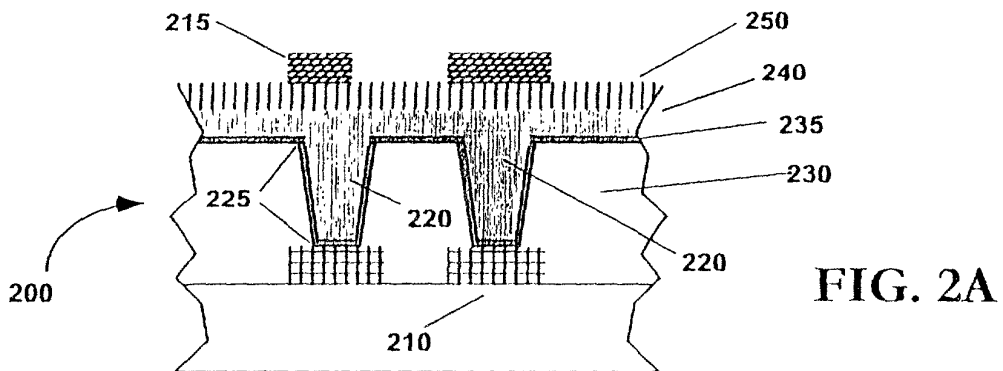


FIG. 1C



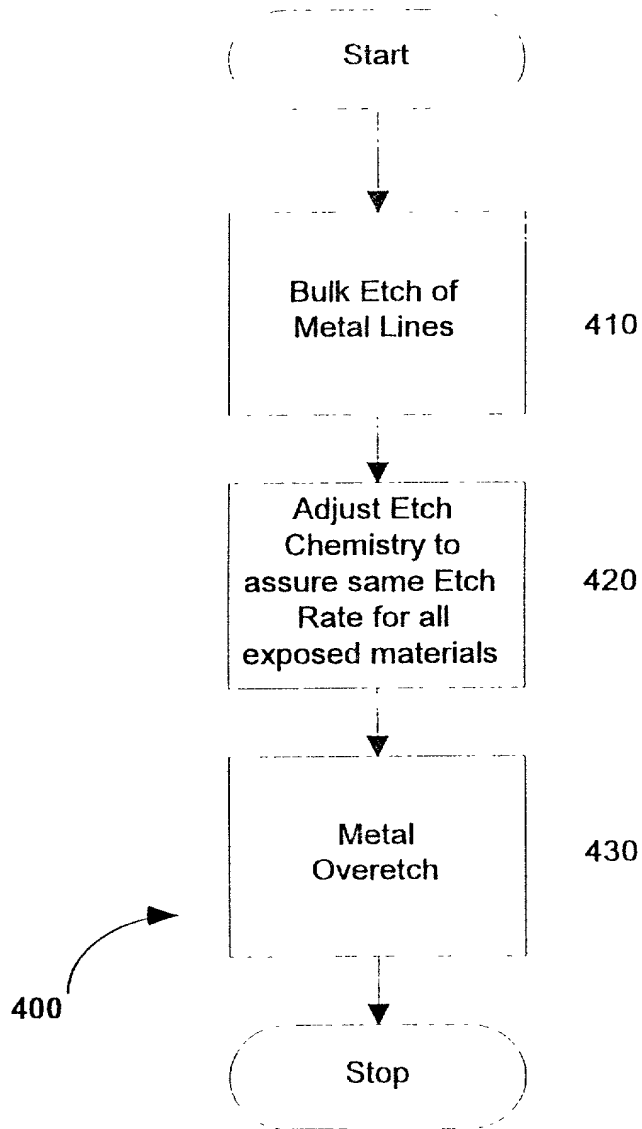


FIG. 3

Main etch chamber	TiN +		AlCu		Copper		Ti +	
	AlCu Bulk		Endpoint		Residue		1:1:1 Overetch	
	Step 01	Step 02	Step 03	Step 04	Step 05	Step 06	Step 07	Step 08
Pressure (mT)	0.00	10.00	10.00	10.00	10.00	10.00	0.00	0.00
RF-Top (W)	0	0	360	360	360	360	0	0
RF-Bottom (W)	0	0	100	225	225	100	0	0
Gap (cm)	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A
BCl3 (sccm)	40.0	40.0	40.0	40.0	50.0	50.0	0.0	0.0
Cl2 (sccm)	40.0	40.0	40.0	40.0	30.0	30.0	0.0	0.0
SF6 (sccm)	0.0	0.0	0.0	0.0	0.0	20.0	0.0	0.0
He clamp (%)	0.0	10.0	10.0	10.0	10.0	10.0	0.0	0.0
Completion	Stabil	Stabil	Time	EndPt	Time	Time	Time	End
Time	30s	30s	24s	50s	5s	50s	10s	s
Channel				262 nm				
Delay (sec)				14				
Norm (sec)				2				
Norm value				0				
Trigger (%)				90				
Electrode Temp	50.0°C							
Chamber Temp	60.0°C							

FIG. 4